

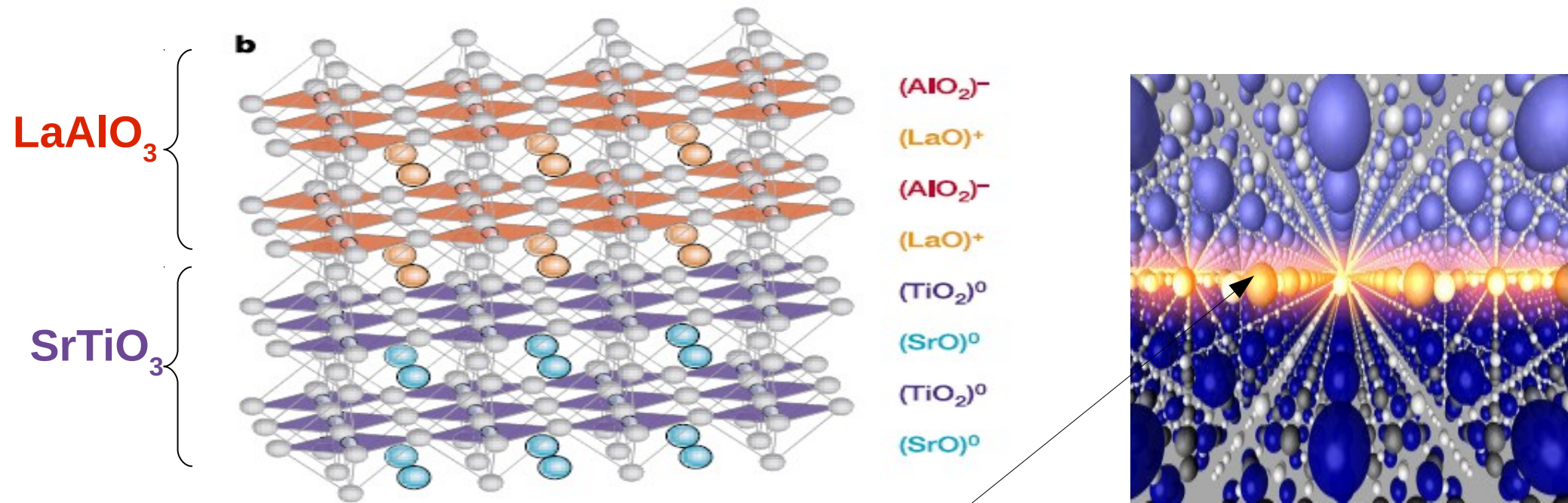
TWO-DIMENSIONAL CONDUCTIVITY AT $\text{LaAlO}_3/\text{SrTiO}_3$ INTERFACES

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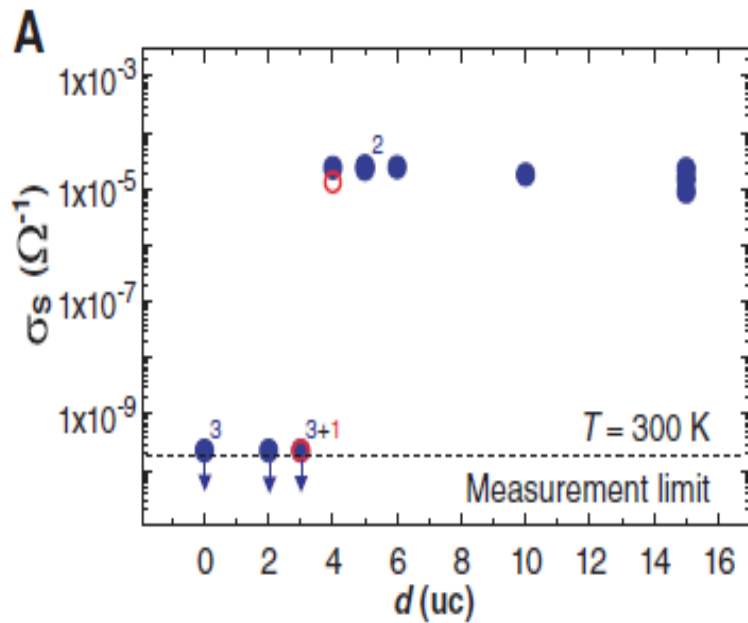
LaAlO₃/SrTiO₃ INTERFACES



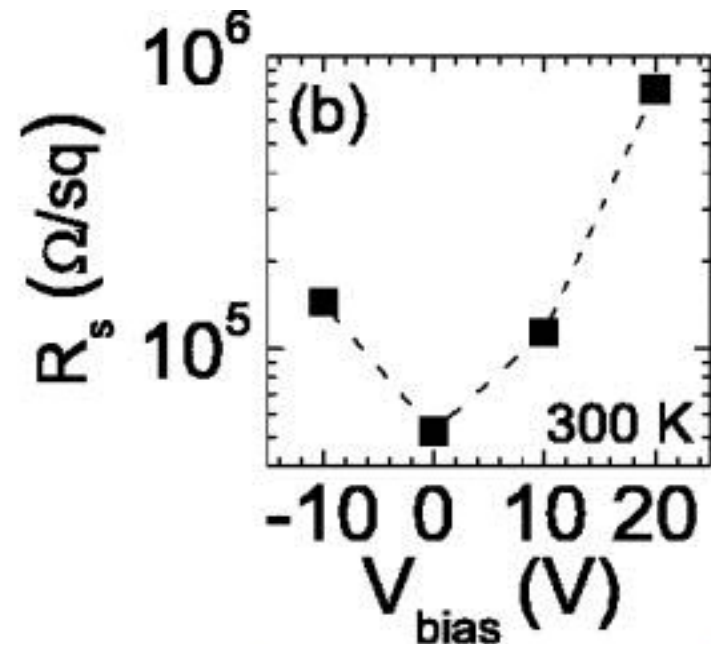
A. Ohtomo, H. Hwang, Nature 427, 423
(2004)

Conducting Interface OR Two-dimensional electron gas(2DEG)

Conductivity at the $\text{LaAlO}_3/\text{SrTiO}_3$ interface



S. Thiel et al., Science 313, 1942(2006)



F. Trier et al., App. Phys. Lett. 103(2013)

Study conductivity at the $\text{LaAlO}_3/\text{SrTiO}_3$ interface Theoretically

Theoretical Model

1- Write the Hamiltonian for the SrTiO₃ film

$$\hat{H} = \hat{H}_0 + \hat{V}_{ext} + \hat{V}_C$$

The **non-interacting Hamiltonian**

$$\hat{H}_0 = \sum_{ij} \sum_{\alpha,\beta} \sum_{\sigma} c_{i\alpha\sigma}^{\dagger} t_{i\alpha,j\beta} c_{j\beta\sigma}$$

$\alpha \longrightarrow$ Ti t_{2g} orbitals, d_{xy}, d_{xz} and d_{yz}

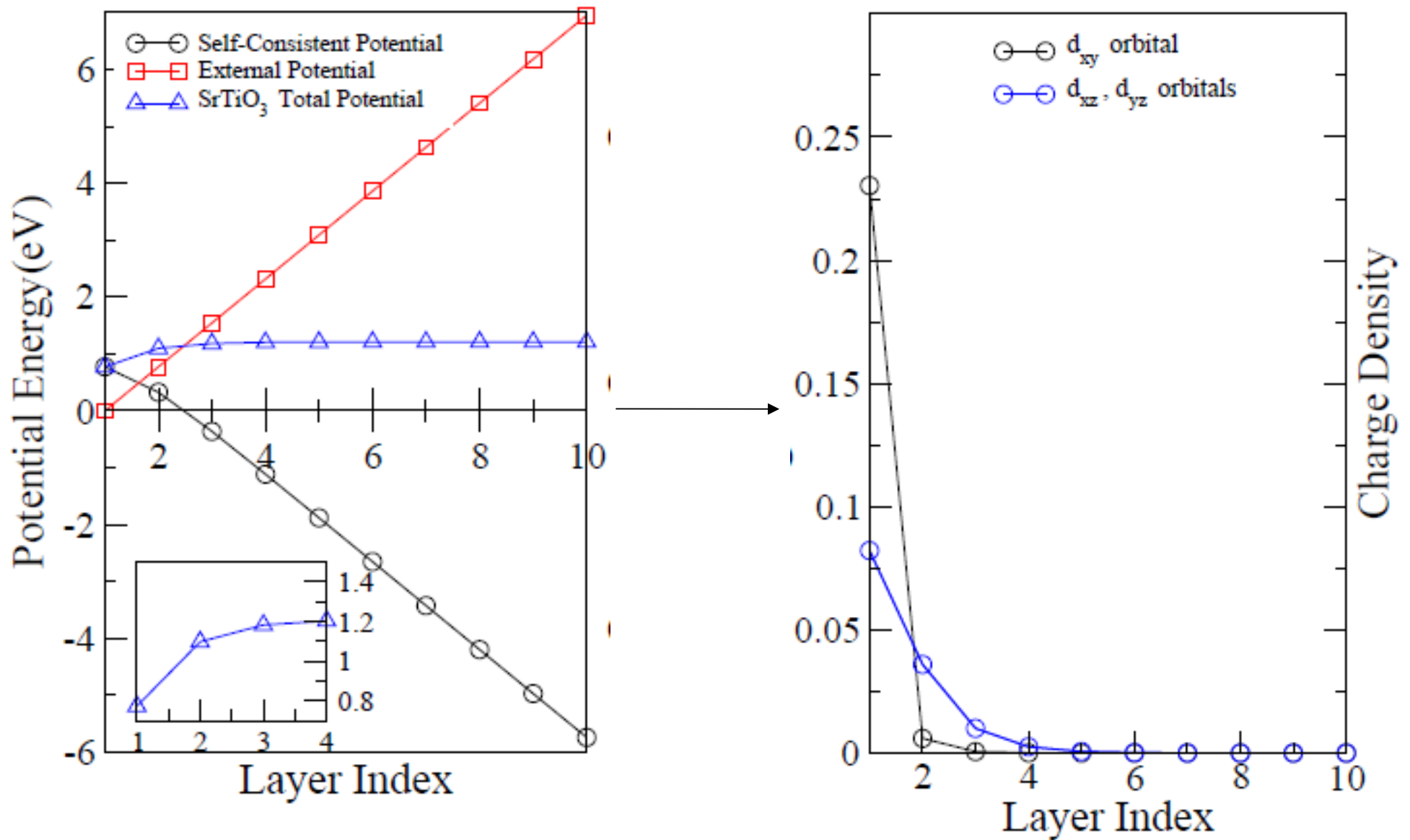
The **Coulomb potential energy**

$$\hat{V}_C = \frac{-e^2 a}{2\epsilon_0 k} \sum_{i_z\alpha\sigma} \sum_{j_z} \sum_{\beta} (|i_z - j_z| - j_z) n_{j_z\beta\sigma} \hat{n}_{i_z\alpha\sigma}$$

The **external potential energy** due to the charge at the LaAlO₃ surface

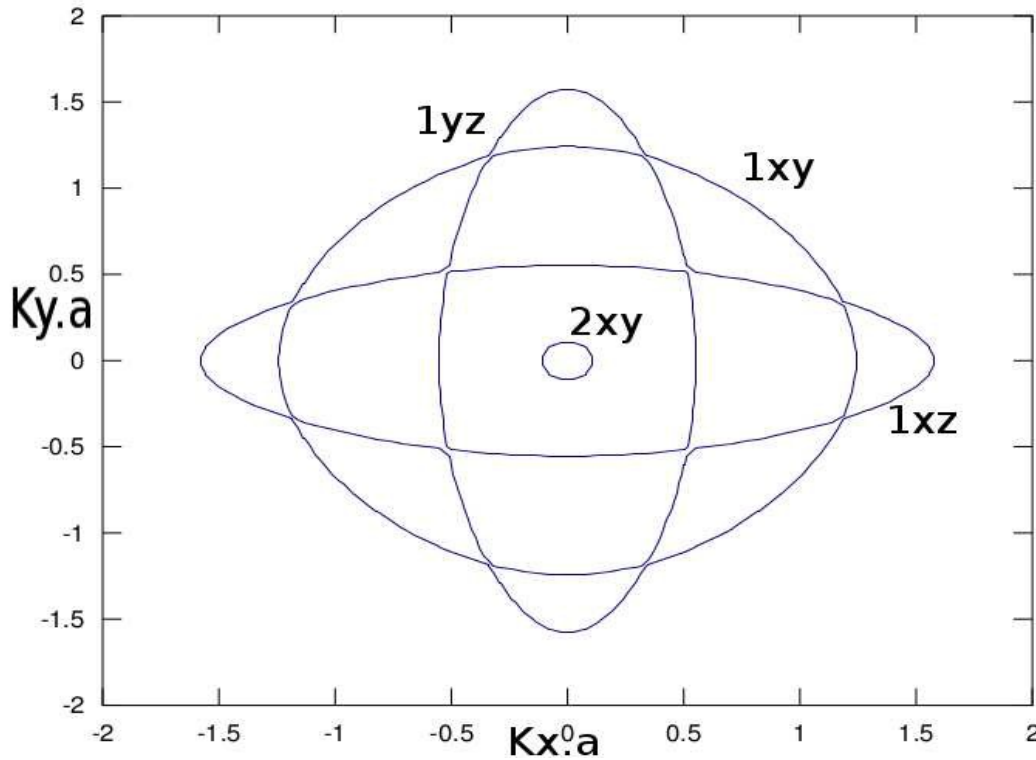
$$\hat{V}_{ext} = \sum_{i_z\alpha\sigma} \varphi_{i_z\alpha}^{ext} \hat{n}_{i_z\alpha\sigma}$$

Self-Consistent Results



The self-consistent solutions for the total potential energy and the charge density inside the SrTiO₃ film

Theoretical Model



- ✓ There are four occupied bands, two with d_{xy} orbital character, and one each with d_{xz} and d_{yz} orbital character.

Fermi surfaces for a Fermi energy $E_f = 0.15\text{eV}$

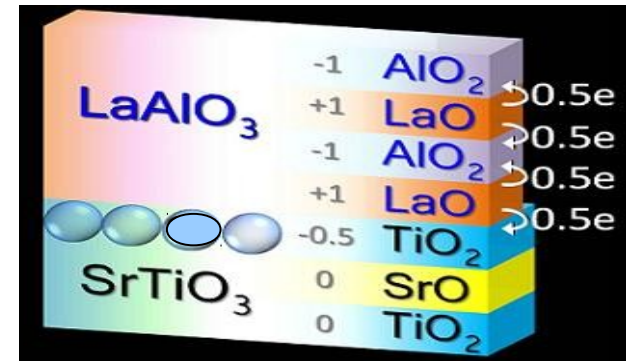
The next step is study the contribution of these four occupied bands to the interface conductivity

Theoretical Model

2- Develop the model for impurities to study the interface conductivity

We assume that

- A low density of point-like impurities with Potential \tilde{V}_{imp}
- Impurities lie at the interface



The relative two-dimensional conductivity of each occupied band as a function in \tilde{V}_{imp}

$$\sigma_{xx}^{(n)}(\tilde{V}_{imp}) = \sqrt{\frac{m_y^n}{m_x^n}} \frac{\epsilon_f^n}{\gamma^n(\tilde{V}_{imp})}$$

$$\sigma_{xx}^{(n)}(\tilde{V}_{imp}) = \sqrt{\frac{m_y^n}{m_x^n}} \frac{\varepsilon_f^n}{\gamma^n(\tilde{V}_{imp})}$$

Where

$\sigma_{xx}^{(n)}$ The two-dimensional conductivity due to band n

$\sqrt{\frac{m_y^n}{m_x^n}}$ The effective mass ratio for band n

$\varepsilon_f^n = (\varepsilon_f - \varepsilon_{n0})$ The relative Fermi energy to the bottom of the band n

γ^n The scattering rate for electrons in band n

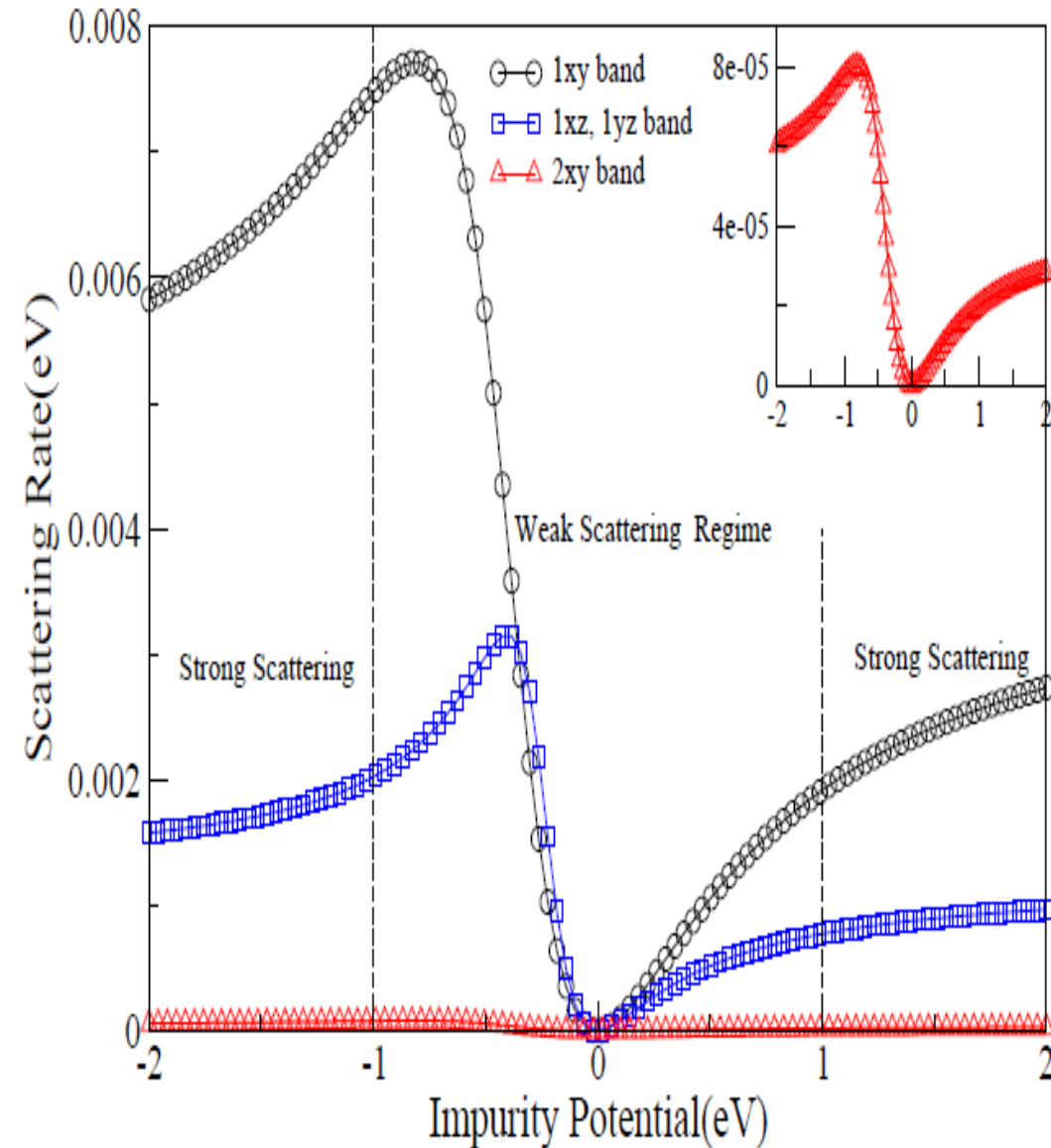
$$\gamma^n(\tilde{V}_{imp}) = -cIm \sum_{\alpha} |\psi_{1\alpha n}(\Gamma)|^2 \underbrace{t_{1\alpha,1\alpha}(\tilde{V}_{imp})}_{\text{Impurity at the interface in orbital } \alpha}$$

Impurity density

Impurity at the interface
in orbital α

How γ^n Changes with \tilde{V}_{imp} ?!

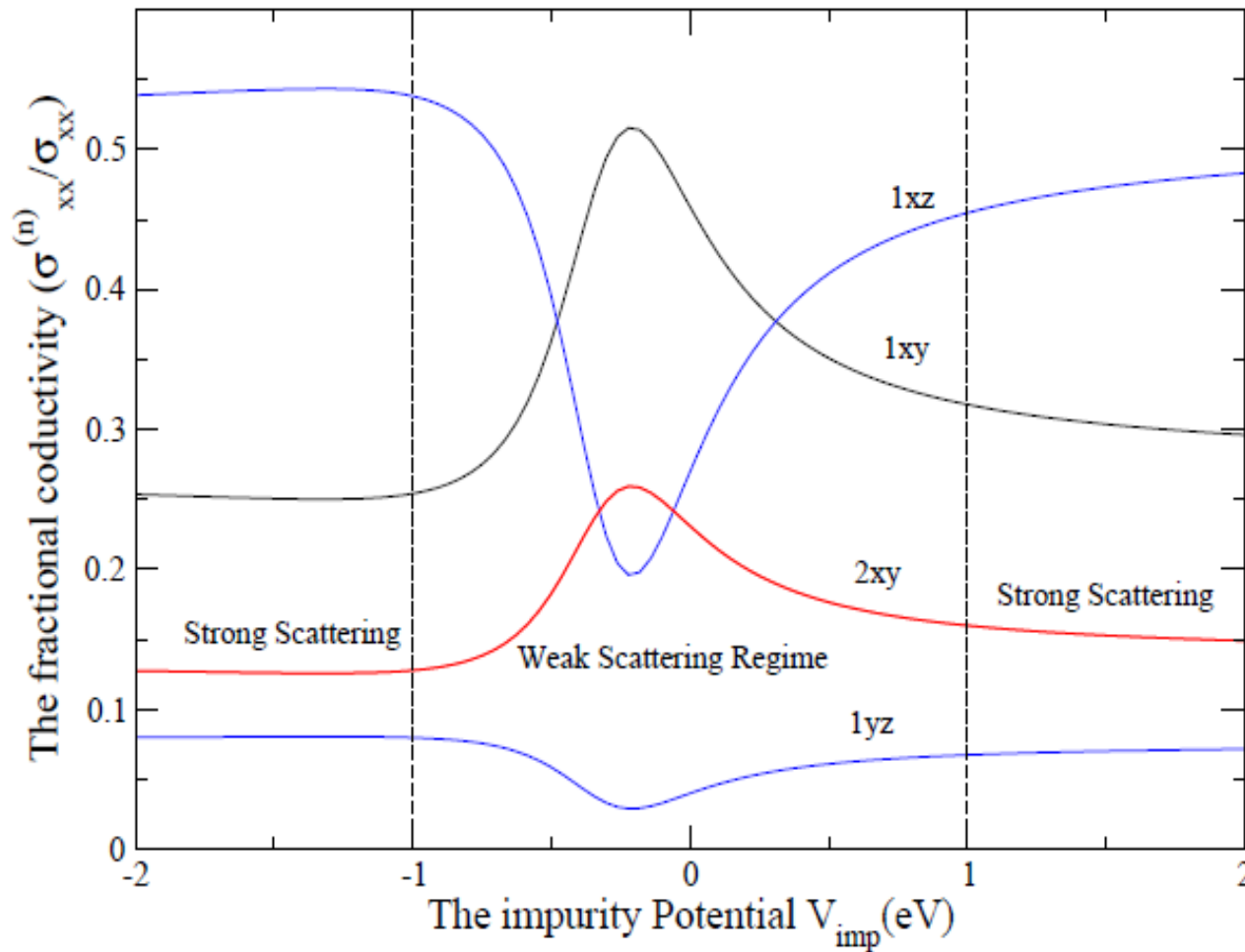
$$\gamma^n(\tilde{V}_{\text{imp}}) = -c \text{Im} \sum_{\alpha} |\psi_{1\alpha n}(\Gamma)|^2 t_{1\alpha,1\alpha}(\tilde{V}_{\text{imp}})$$



- Similar dependences of all bands on
- Two Scattering regimes:
 - Weak Scattering
 - Strong Scattering
- **1xy** band largest scattering rate
- **2xy** band smallest scattering rate
- **1xz & 1yz** bands same scattering rate

The Fractional Conductivity

$$\sigma_{xx}^{(n)}(\tilde{V}_{imp}) = \sqrt{\frac{m_y^n}{m_x^n}} \frac{\epsilon_f^n}{\gamma^n(\tilde{V}_{imp})}$$



Band	$\sqrt{\frac{m_y}{m_x}}$	$\epsilon_f^n (eV)$
1xy	1	0.319
1yz	0.385	0.069
1xz	2.597	0.069
2xy	1	0.001

Three parameters control the contribution of each band to the total two-dimensional conductivity

Summary

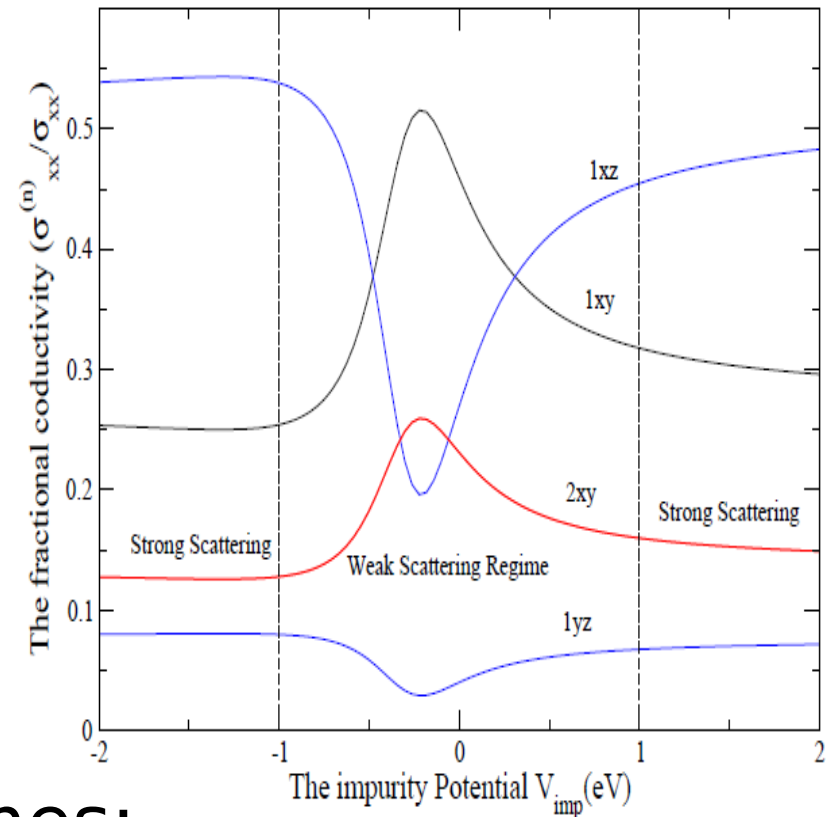
* The contribution of the occupied bands to the interface conductivity depends on three main parameters;

The impurity potential
The effective mass ratios
The relative Fermi energy

* There are two scattering regimes:

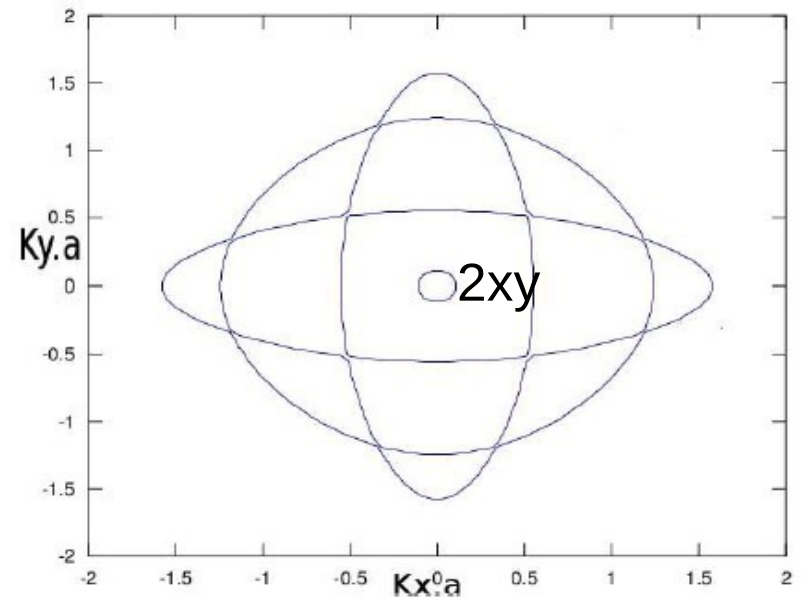
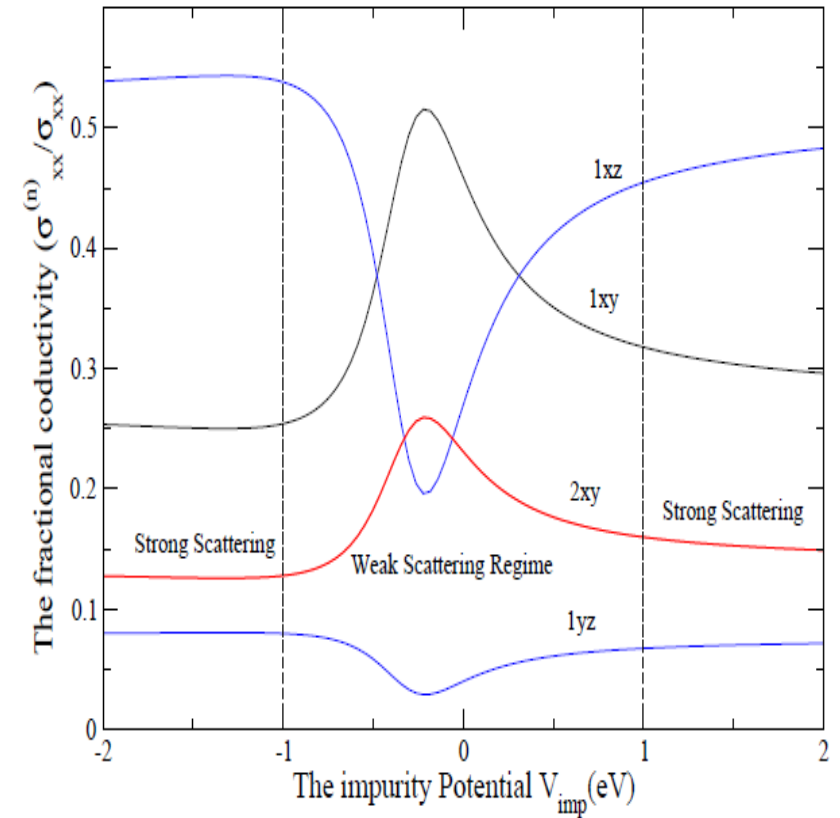
the **weak scattering** regime in which the **1xy** and **2xy** band contributions are dominant, and

the **strong scattering** regime in which the **1xz** band has the largest fractional conductivity.



Summary

*The **2xy** band makes a remarkably large contribution to the two-dimensional conductivity, even though it has the smallest Fermi surface.



THANK YOU